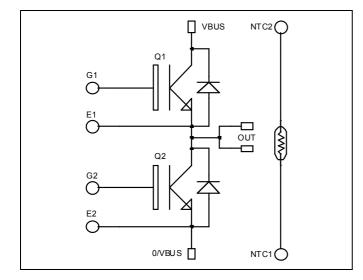


APTGT100A170TG

Phase leg Trench + Field Stop IGBT3 Power Module



#### $\mathbf{O}$ (0) 0 G2 🛙 OUT Ο E2 🕯 VBUS 0/VBUS OUT 0 E1 E2 🛙 NTC2 0 G2 🕻 NTC1 🛿 $\bigcirc$ GI L.C.

## $V_{CES} = 1700V$ $I_{C} = 100A$ @ Tc = 80°C

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
    - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
    - Very low stray inductance
    - Symmetrical design
      - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

#### Benefits

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- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
  - Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

## Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1700	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	150	
I <sub>C</sub>	Continuous Collector Current	$T_C = 80^{\circ}C$	100	А
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
$V_{GE}$	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Maximum Power Dissipation	$T_C = 25^{\circ}C$	560	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	200A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μA
V	Collector Emitter Saturation Voltage	J I I I I I I I I I I I I I I I I I I I	$T_j = 25^{\circ}C$		2.0	2.4	V
V <sub>CE(sat)</sub>			$T_{j} = 125^{\circ}C$		2.4		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			9		
Coes	Output Capacitance				0.36		nF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.3			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	ning (25°C)		370		
T <sub>r</sub>	Rise Time	$V_{GE} = 15V$			40		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 100A$			650		ns
$T_{\rm f}$	Fall Time	$R_G = 4.7 \Omega$		180		L	
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch		400			
Tr	Rise Time	$V_{GE} = 15V$ $V_{Bus} = 900V$ $I_{C} = 100A$ $R_{G} = 4.7 \Omega$			50		
T <sub>d(off)</sub>	Turn-off Delay Time				800		ns
$T_{f}$	Fall Time				300		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$	$T_j = 125^{\circ}C$		32		mI
E <sub>off</sub>	Turn-off Switching Energy	$I_{\rm C} = 100 \text{A}$ $R_{\rm G} = 4.7 \ \Omega$	$T_j = 125^{\circ}C$		31		mJ

## **Diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1700			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1700V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			250 500	μΑ
$I_{\rm F}$	DC Forward Current		$T_{j} = 125 \text{ C}$ $T_{c} = 80^{\circ}\text{C}$		100	500	А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$	$T_{i} = 25^{\circ}C$ $T_{i} = 125^{\circ}C$		1.8 1.9	2.2	V
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 100A$ $V_R = 900V$ di/dt =1000A/µs	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$		385 490		ns
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$		25 42		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$ $T_j = 125^{\circ}C$		11 21		mJ



# APTGT100A170TG

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
	<i>D</i>				

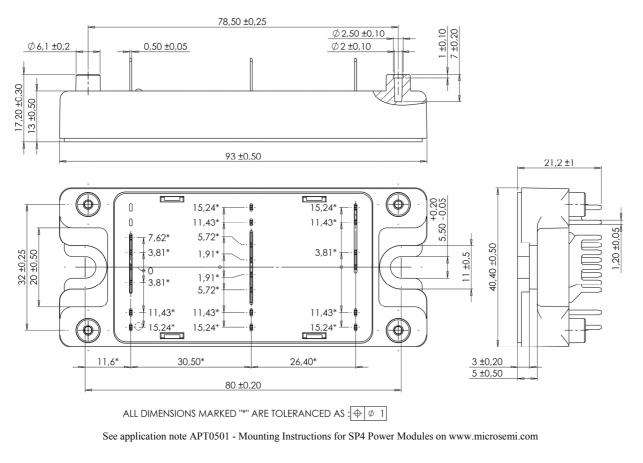
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermis

Thermistor temperature T: Thermistor value at T

### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.22	°C/W
<b>R</b> <sub>th</sub> JC		Diode			0.39	C/W	
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range		-40		125	°C	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

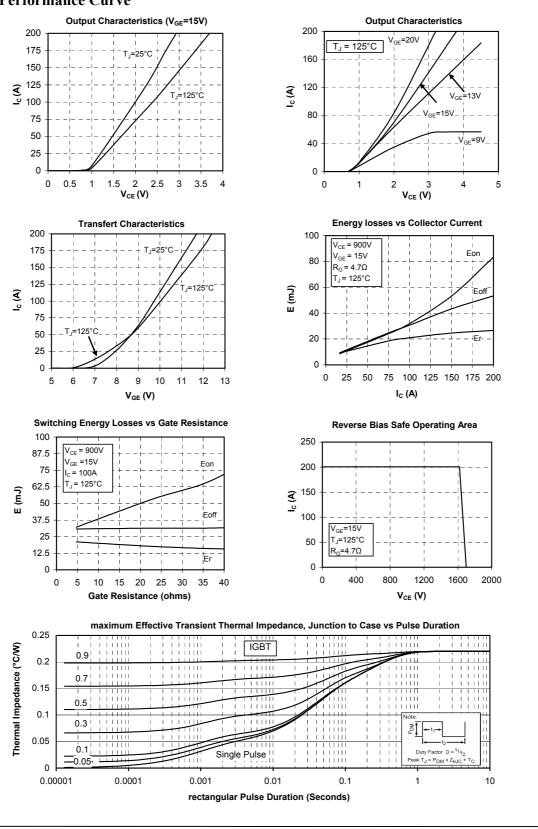
### SP4 Package outline (dimensions in mm)





#### **Typical Performance Curve**

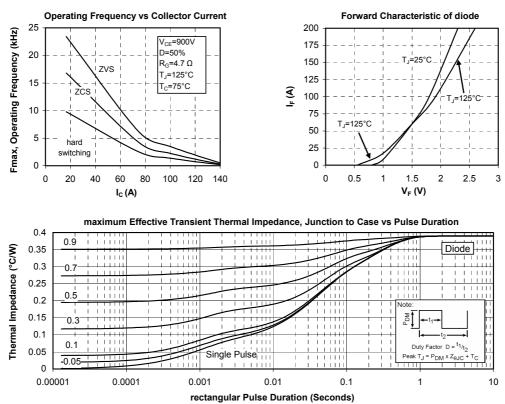
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## **APTGT100A170TG**



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